

## **Notification about the transfer of the semiconductor business**

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

※ Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

**Nuvoton Technology Corporation Japan**

**SK8603190L**

Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance : RDS(on) typ = 10 mΩ (VGS = 4.5 V)
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : 19

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

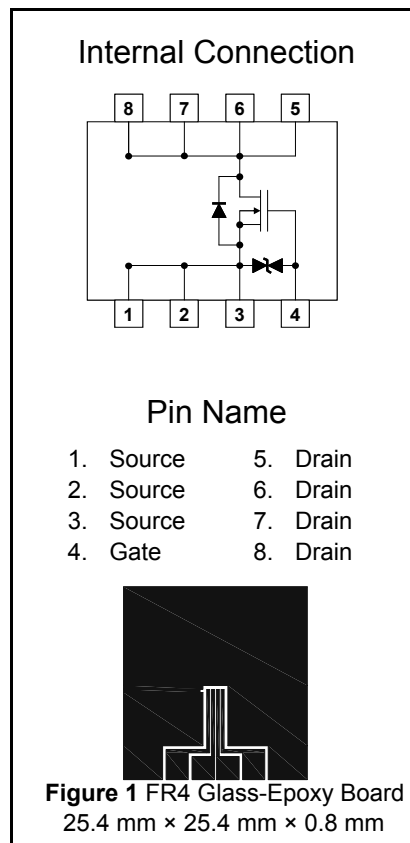
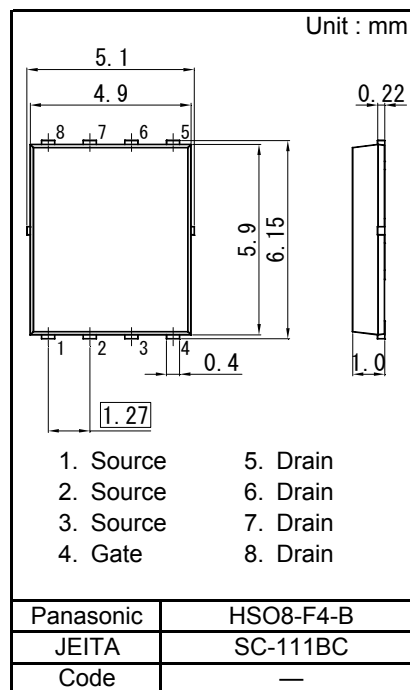
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	VDS	30	V
Gate to Source Voltage	VGS	±20	
Drain Current	ID	Ta = 25 °C, t = 10 s <sup>*1</sup>	16
		Ta = 25 °C, DC <sup>*1</sup>	12
		Tc = 25 °C	19
		Pulsed, Tch < 150 °C <sup>*2</sup>	48
Total Power Dissipation	PD	Ta = 25 °C, DC <sup>*1</sup>	2.7
		Tc = 25 °C	19
Thermal Resistance	Channel to Ambient	Rth(ch-a)	45
	Channel to Case	Rth(ch-c)	6.6
Channel Temperature	Tch	150	°C
Operating ambient temperature	Topr	-40 to +85	
Storage Temperature Range	Tstg	-55 to +150	
Avalanche Current (Single pulse) <sup>*3</sup>	IAR	8	A
Avalanche Energy (Single pulse) <sup>*3</sup>	EAR	8	mJ

Note \*1 Device mounted on a glass-epoxy board in Figure 1

\*2 Pulse test: Ensure that the channel temperature does not exceed 150 °C

\*3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 °C (initial)



■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μA
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = 1.01 mA, VDS = 10 V	1		3	V
Drain-source On-state Resistance	RDS(on)1	ID = 8 A, VGS = 10 V		7	10	mΩ
	RDS(on)2	ID = 8 A, VGS = 4.5 V		10	14	

Dynamic Characteristics

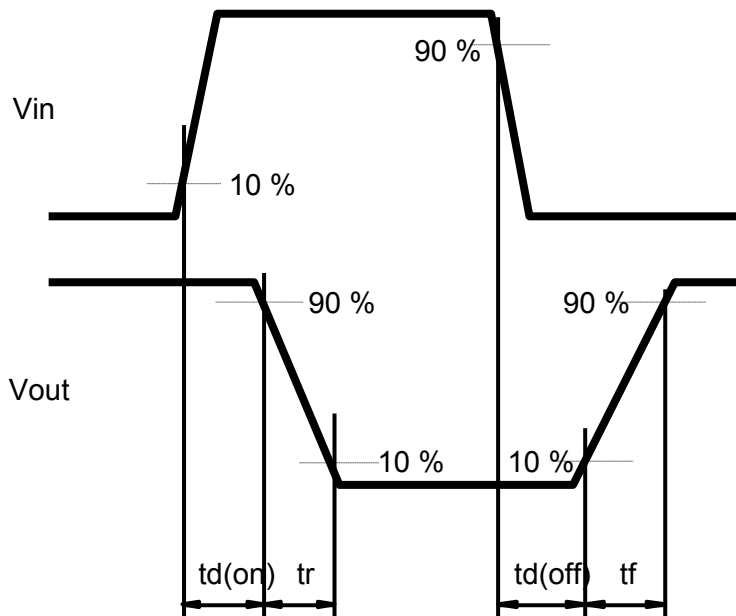
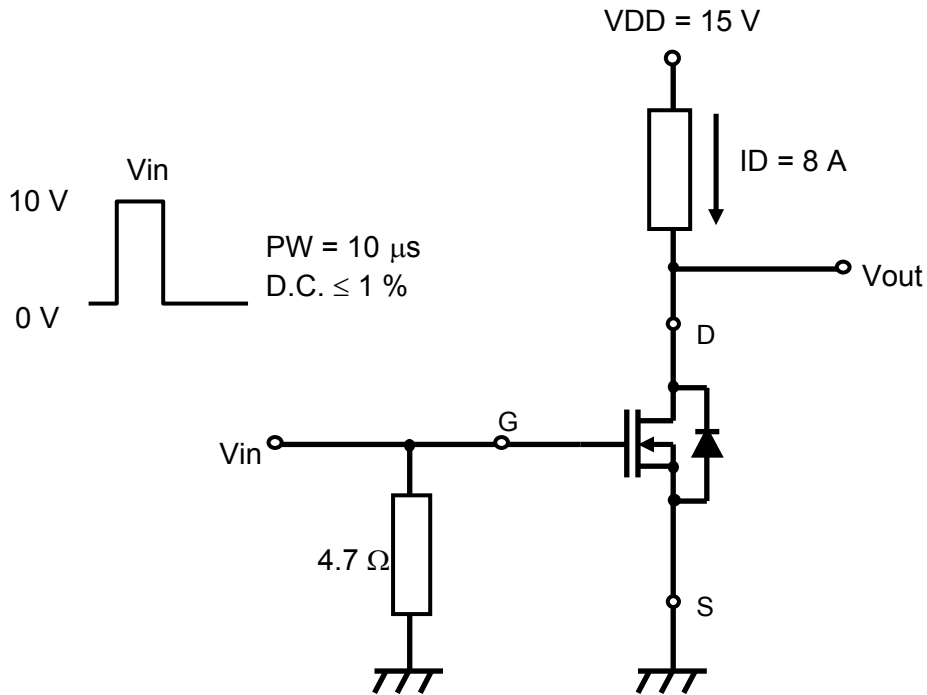
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz		780	1 092	pF
Output Capacitance	Coss			160	224	
Reverse Transfer Capacitance	Crss			61	98	
Turn-on Delay Time <sup>*1</sup>	td(on)	VDD = 15 V, VGS = 0 to 10 V		7		ns
Rise Time <sup>*1</sup>	tr	ID = 8 A		3		
Turn-off Delay Time <sup>*1</sup>	td(off)	VDD = 15 V, VGS = 10 to 0 V		34		ns
Fall Time <sup>*1</sup>	tf	ID = 8 A		4		
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V ID = 8 A		6.3		nC
Gate to Source Charge	Qgs			2.5		
Gate to Drain Charge	Qgd			2.1		
Gate resistance	rg	f = 5 MHz		1.2	3	Ω

Body Diode Characteristic

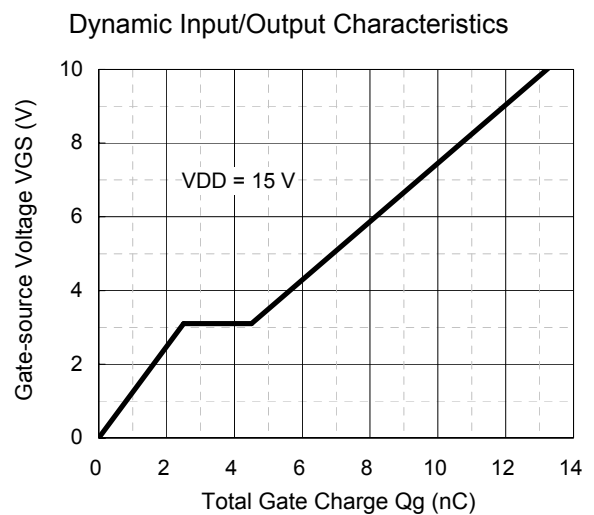
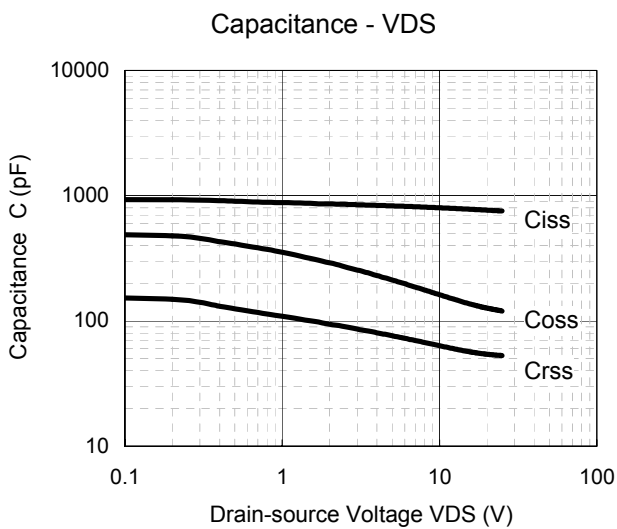
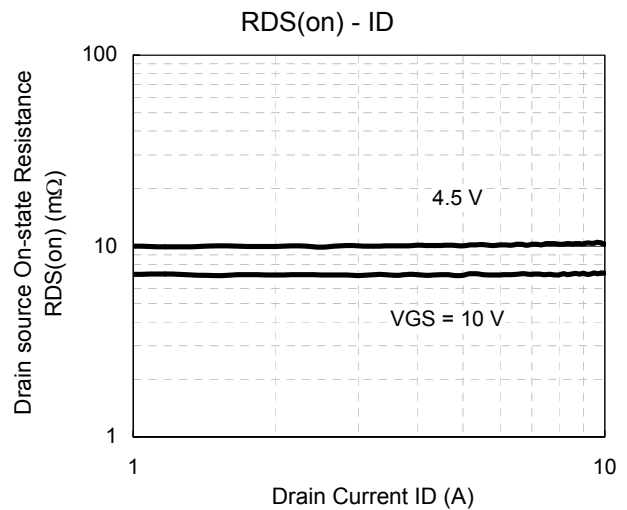
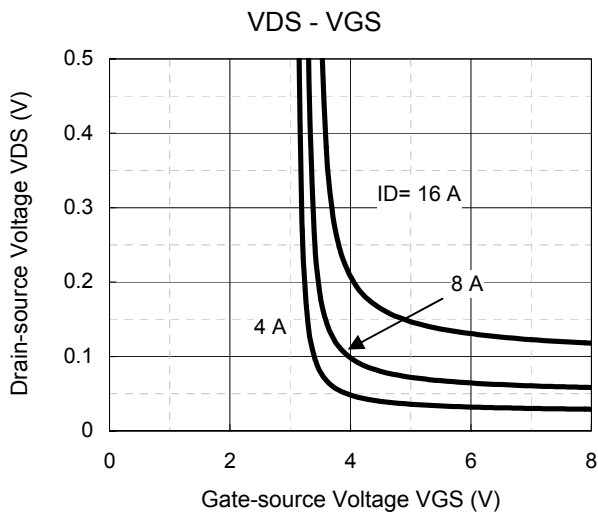
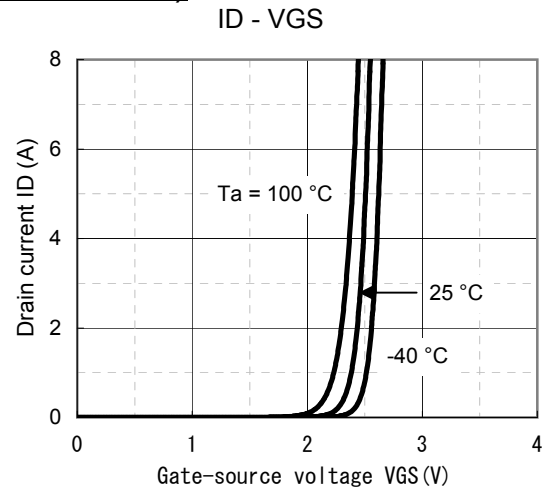
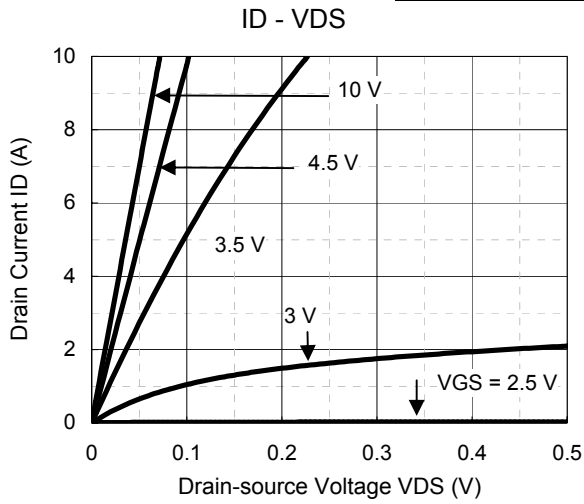
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	VSD	IS = 8 A, VGS = 0 V		0.8	1.2	V

Note : 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.  
2. \*1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

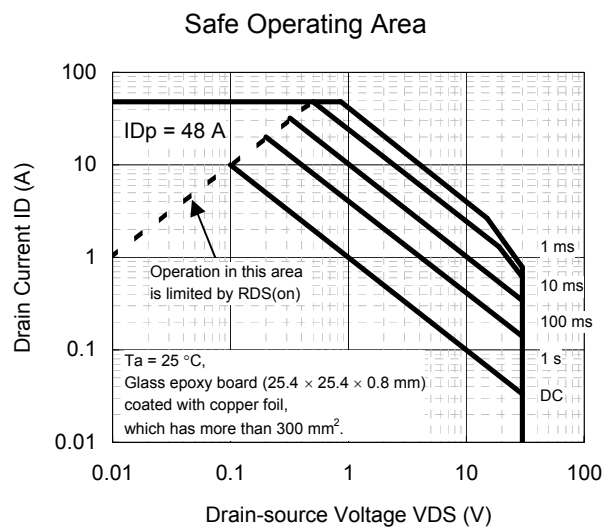
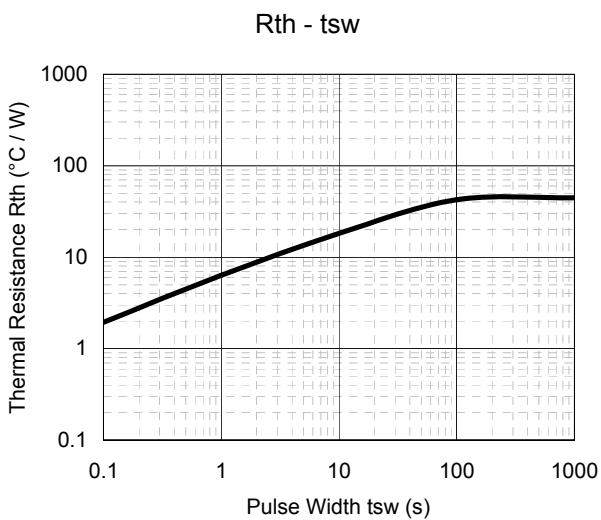
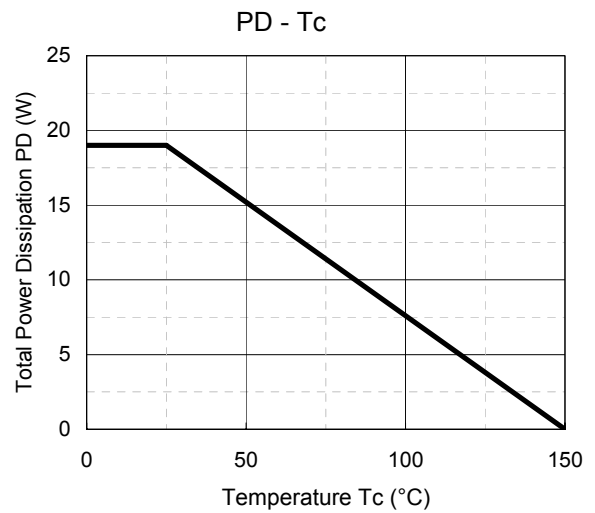
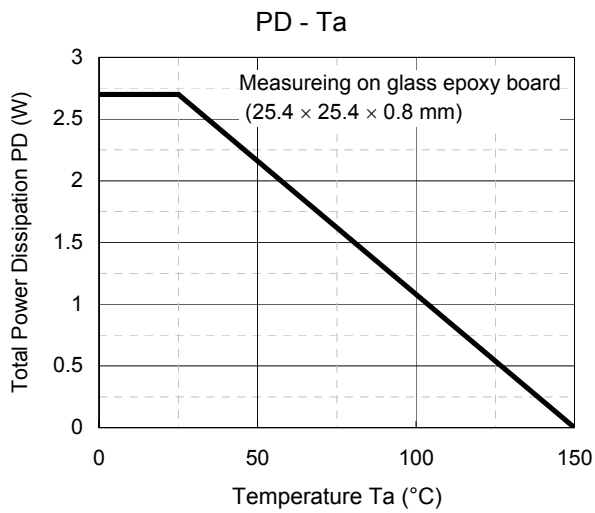
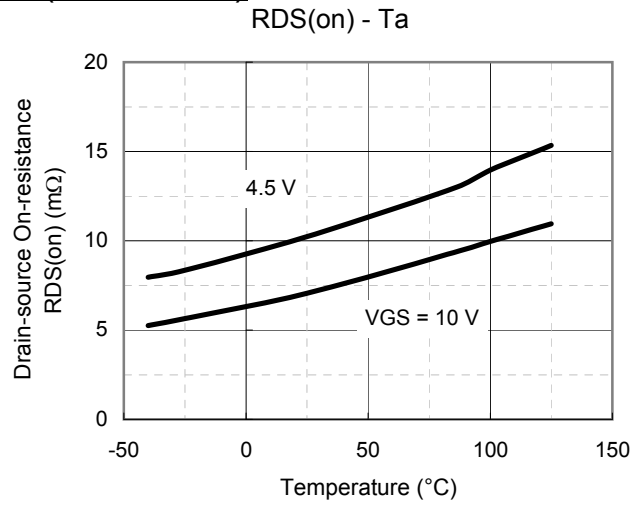
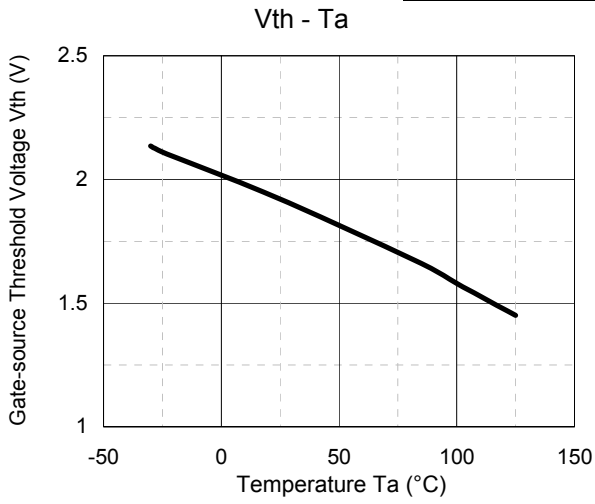
\*1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



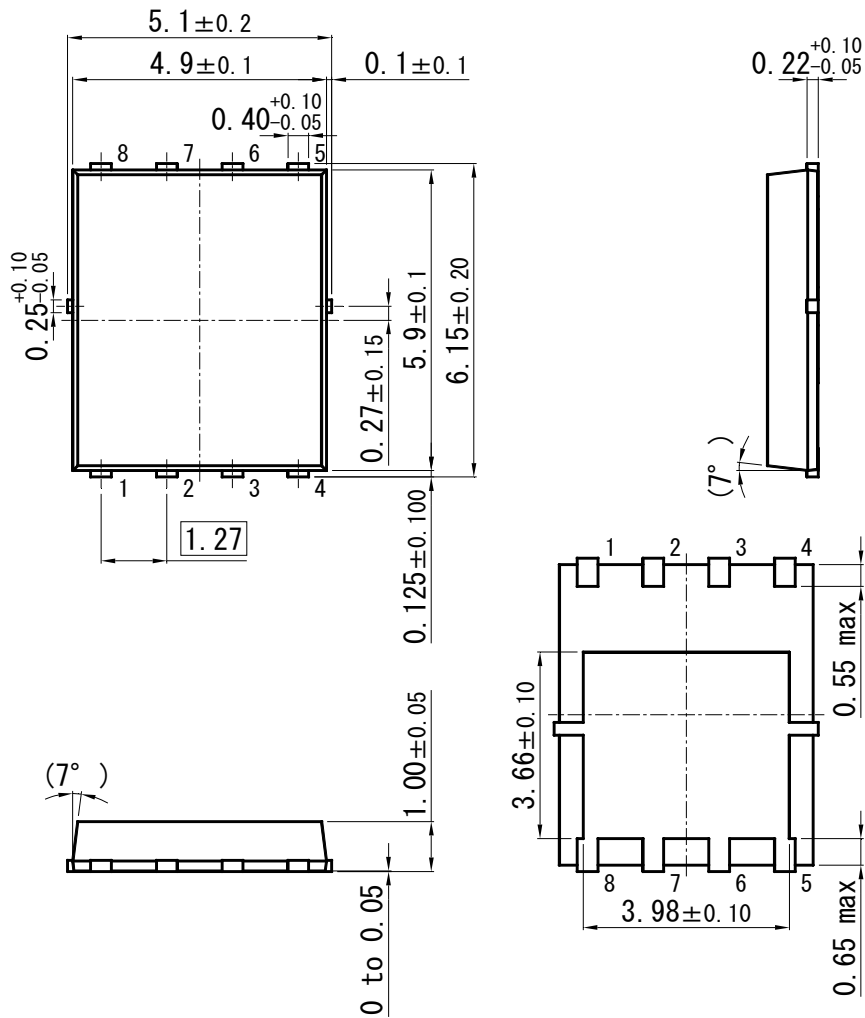
Technical Data ( reference )



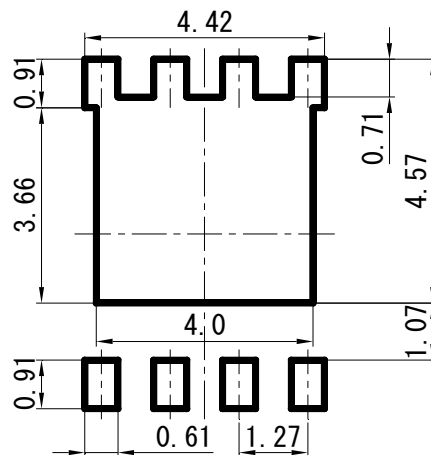
Technical Data ( reference )



HSO8-F4-B



■ Land Pattern (Reference) (Unit : mm)



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